

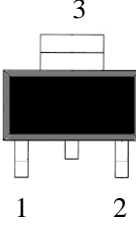

1、Description1、 Description

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive SOT-223 package which is readily adaptable for use in automatic insertion equipment. Sensitive Gate Triggering In Four Trigger Modes for all possible Combinations of Trigger Sources, and Especially for Circuits that Source Gate Drives

2、 Features

- Blocking voltage to 800V
- On-state RMS current to 1.0 A
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Low cost package.

3、 Pinning information

PIN	Description	Simplified outline	Symbol
1	main terminal 1(T1)		
2	Gate(G)		
3	main terminal 2(T2)		

4、 Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
V_{DRM} & V_{RRM}	Repetitive peak off-state voltages	800	V
$I_{T(RMS)}$	RMS on-state current	1.0	A
I_{TSM}	Non-repetitive peak on-state current	12	A

5、 Thermal characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction to Case	<i>in free air</i>	-	-	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	<i>in free air</i>	-	-	200	°C/W
T_L	Maximum Lead Temperature for Soldering Purposes for 10 Seconds	<i>in free air</i>	-	-	260	°C

6、Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_{DRM} & V_{RRM}	Repetitive peak off-state voltages		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz ($T_C = +50^\circ\text{C}$)	-	-	1.0	A
I_{TSM}	Non-repetitive peak on-state current	One Full Cycle, Sine Wave 60 Hz ($T_C = 110^\circ\text{C}$)	-	-	12	A
I^2t	I^2t for fusing	$t = 8.3\text{ ms}$	-	-	0.72	A^2s
I_{GM}	Peak gate current		-	-	1.0	A
V_{GM}	Peak gate voltage		-	-	5.0	V
P_{GM}	Peak gate power		-	-	1.0	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	-	0.1	W
T_{stg}	Storage temperature		-40	-	150	$^\circ\text{C}$
T_j	Operating junction temperature		-40	-	125	$^\circ\text{C}$

7、Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
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Static characteristics

I_{DRM} I_{RRM}	Peak Repetitive Forward Or Reverse Blocking Current	$V_D = \text{Rated } V_{DRM} \text{ and } V_{RRM}, R_{GK} = 1\text{K}\Omega$ $T_C = 25^\circ\text{C}$ $T_C = 110^\circ\text{C}$	- -	- -	5 100	μA μA
I_{GT}	Gate trigger current	($V_D = 12\text{ Vdc}, R_L = 100\text{ Ohms}$) T2+ G+ T2+ G- T2- G- T2- G+	- - - -	1.5 2.5 2.0 5.0	3 3 3 7	mA mA mA mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	- - - -	10 20 10 10	mA mA mA mA
I_H	Holding current	$V_D = 12\text{ V};$ Initiating Current = 200 mA, Gate Open	-	2.5	5.0	mA
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	1.0 0.85 0.80 1.3	1.5 1.5 1.5 1.5	V V V V
V_{GD}	Off-state leakage Voltage	$V_D = 12\text{ V}, R_L = 100\text{ Ohms}, T_J = 110^\circ\text{C};$ All Four Quadrants	0.1	-	-	V

Dynamic Characteristics

$dv/dt(c)$	Critical Rate-of-Rise of Commutation Voltage	$V_D = \text{Rated } V_{DRM}, I_{TM} = .84\text{ A},$ Commutating $di/dt = .3\text{ A/ms},$ Gate Unenergized, $T_C = 50^\circ\text{C}$	1.5	-	-	V/ μs
dv/dt	Critical Rate of Rise of Off-State Voltage	$V_D = \text{Rated } V_{DRM}, T_C = 110^\circ\text{C},$ Gate Open, Exponential Waveform	25	-	-	V/ μs
t_{gt}	Gate controlled turn-on time	$V_D = \text{Rated } V_{DRM}, I_{TM} = 1.0\text{ A pk}, I_G = 25\text{ mA}$	-	2.0	-	μs

8. Electrical Characteristics Curve

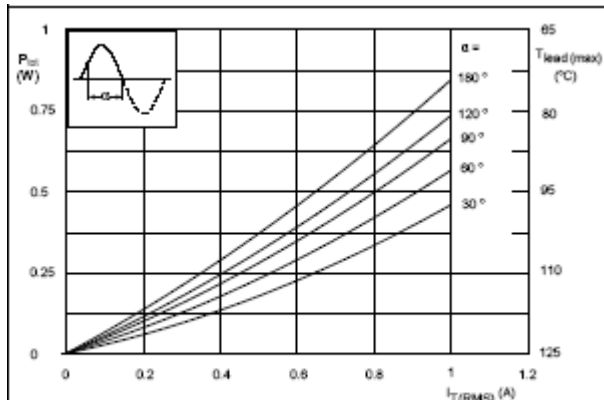


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

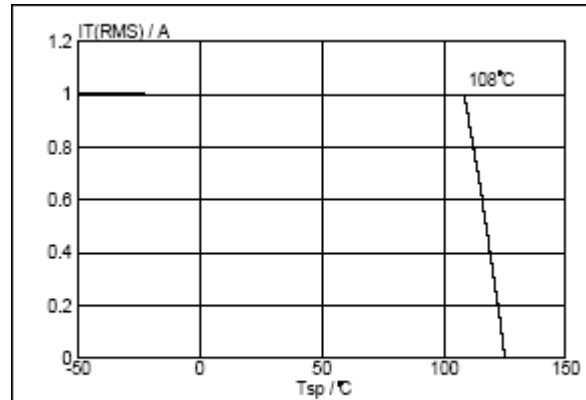


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus lead temperature T_{lead} .

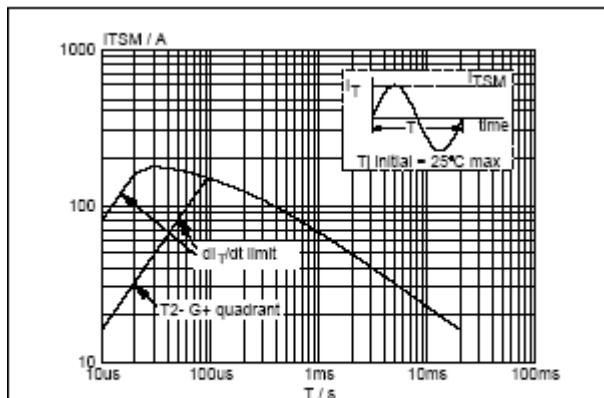


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20ms$.

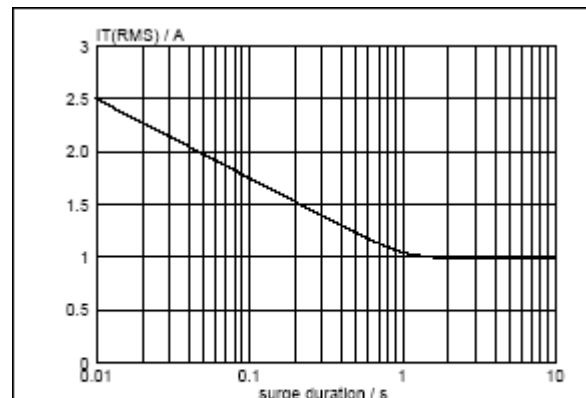


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50 Hz$; $T_{lead} \leq 51^\circ C$.

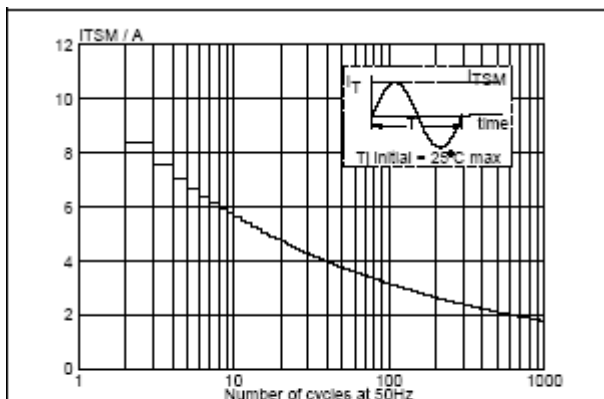


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50 Hz$.

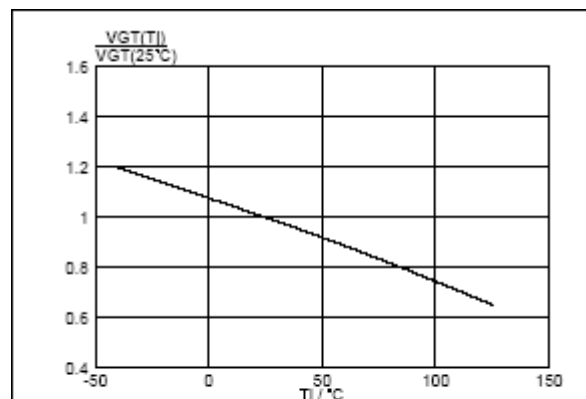
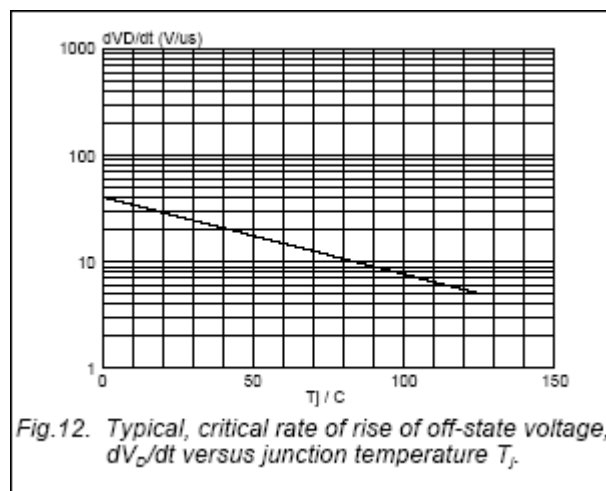
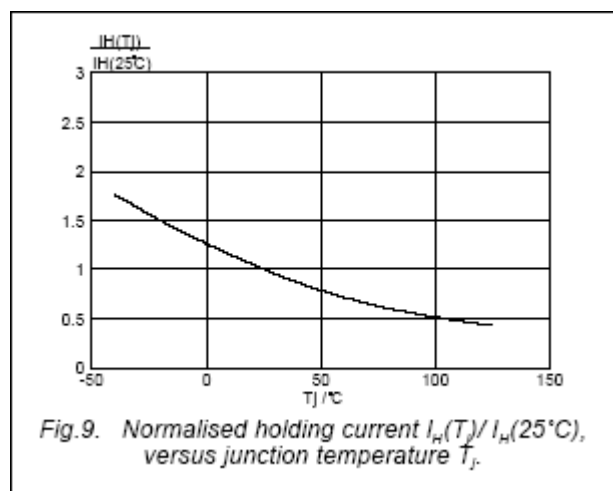
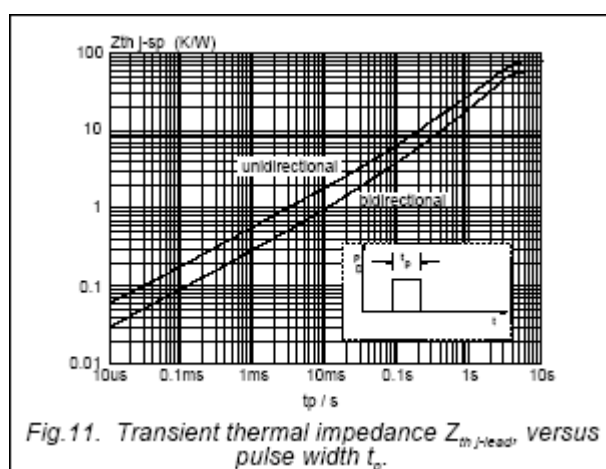
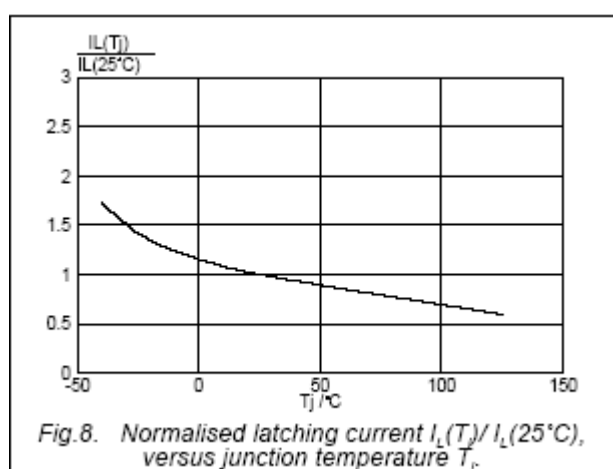
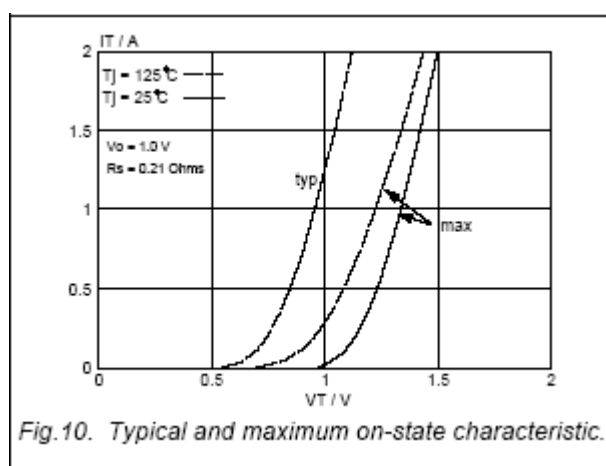
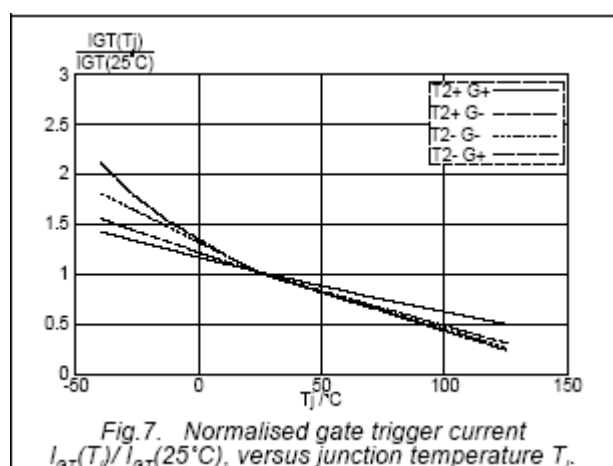
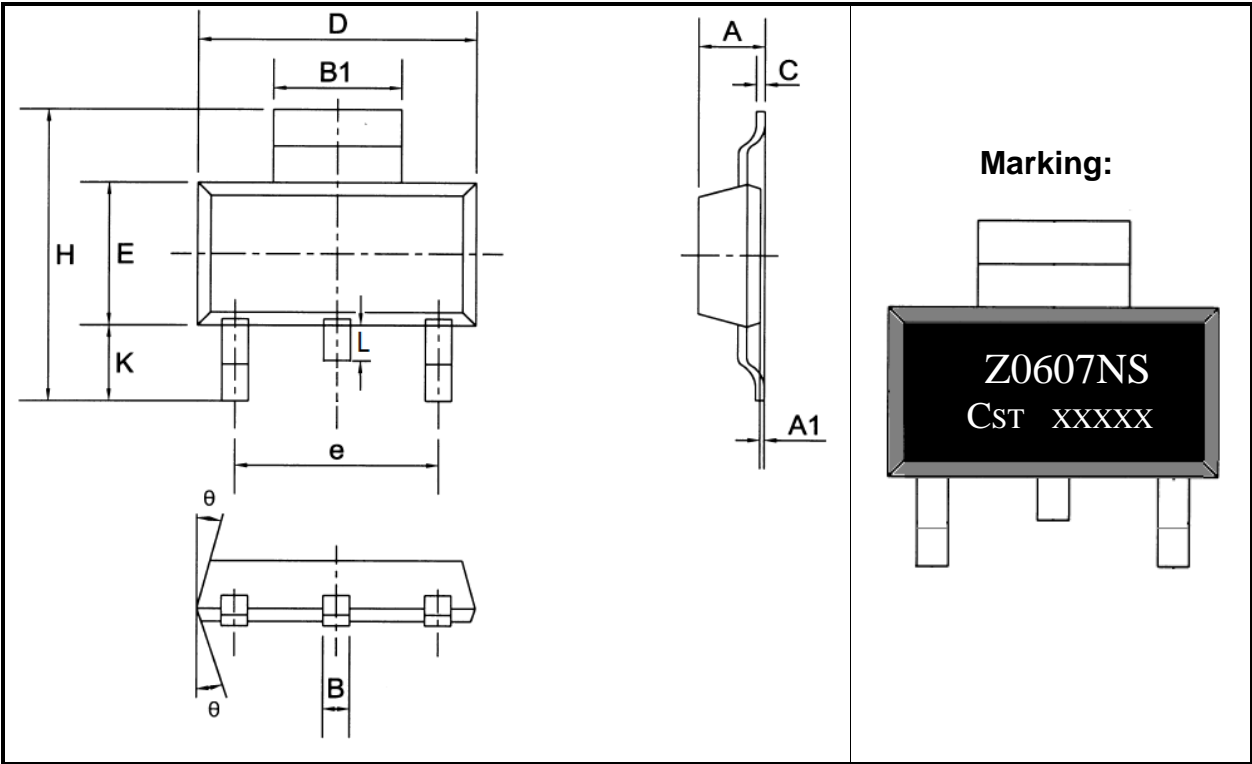


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^\circ C)$, versus junction temperature T_j .



9、Package outline(SOT-223)



DIM	Inches			Millimeters		
	Min	Type	Max	Min	Type	Max
A	0.059	0.063	0.071	1.5	1.6	1.8
A1	0	0.002	0.004	0	0.06	0.10
B1	0.114	0.118	0.122	2.9	3.0	3.1
B	0.024	0.028	0.031	0.6	0.7	0.8
C	0.009	0.010	0.013	0.22	0.26	0.32
D	0.248	0.256	0.264	6.3	6.5	6.7
E	0.130	0.138	0.146	3.3	3.5	3.7
e		0.181			4.6	
K	0.063	0.069	0.083	1.6	1.75	2.1
H	0.264	0.276	0.287	6.7	7.0	7.3
L		0.033			0.85	